

Claim Status

Claims 1-13 (Cancelled)

- 5 14. (Original) A method for forming an emitter, comprising the steps of:
forming a patterned oxide layer to define an emission area upon an
electron supply layer; and
forming a quantum dot zeolite emission layer comprising a plurality of
cages and having semiconductor materials held within said cages.
- 10 15. (Original) The method of claim 14, further comprising a step of forming a metal
contact structure on the patterned oxide layer.
- 15 16. (Original) The method of claim 15, further comprising a step of forming a thin
metal layer on the quantum dot zeolite emission layer and the metal contact
structure.
- 20 17. (Original) The method of claim 15, wherein the metal contact structure
comprises a single metal layer.
18. (Original) The method of claim 15, wherein the metal contact structure
comprises multiple metal layers.
- 25 19. (Original) The method of claim 14, wherein said step of forming an quantum
dot zeolite emission layer comprises forming a zeolite layer having a thickness in
the approximate range of 0.05 – 0.5 micrometers.
- 30 20. (Original) The method of claim 14, performed as part of an integrated circuit
formation process to form the emitter as part of an integrated circuit including
emitter control circuitry.

Claims 21-35 (Cancelled)